Ryota Negishi

List of Publications by Year in descending order

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42 587 12 23
papers citations h-index g-index

44 44 729
all docs docs citations times ranked citing authors

#	Article	IF	CITATIONS
1	Scanning probe analysis of twisted graphene grown on a graphene/silicon carbide template. Nanotechnology, 2022, 33, 155603.	2.6	4
2	Crossover point of the field effect transistor and interconnect applications in turbostratic multilayer graphene nanoribbon channel. Scientific Reports, 2021, 11, 10206.	3.3	3
3	Turbostratic Stacking Effect in Multilayer Graphene on the Electrical Transport Properties. Physica Status Solidi (B): Basic Research, 2020, 257, 1900437.	1.5	13
4	Turbostratic Stacking Effect in Multilayer Graphene on the Electrical Transport Properties. Physica Status Solidi (B): Basic Research, 2020, 257, 2070015.	1.5	2
5	Effect of a protective layer on a carbon nanotube thin film channel in a biosensor device. Japanese Journal of Applied Physics, 2019, 58, SIIB14.	1.5	4
6	Neuromorphic switching behavior in multi-stacking composed of Pt/graphene oxide/Ag ₂ S/Ag. Japanese Journal of Applied Physics, 2019, 58, SIID08.	1.5	1
7	Turbostratic multilayer graphene synthesis on CVD graphene template toward improving electrical performance. Japanese Journal of Applied Physics, 2019, 58, SIIB04.	1.5	35
8	Investigation of surface potentials in reduced graphene oxide flake by Kelvin probe force microscopy. Japanese Journal of Applied Physics, 2018, 57, 06HD02.	1.5	3
9	Biosensor response from target molecules with inhomogeneous charge localization. Journal of Applied Physics, 2018, 124, 064502.	2.5	9
10	Synthesis of very narrow multilayer graphene nanoribbon with turbostratic stacking. Applied Physics Letters, 2017, 110, .	3.3	13
11	Diameter dependence of longitudinal unzipping of single-walled carbon nanotube to obtain graphene nanoribbon. Japanese Journal of Applied Physics, 2017, 56, 06GG12.	1.5	8
12	Improving sensor response using reduced graphene oxide film transistor biosensor by controlling the adsorption of pyrene as an anchor molecule. Japanese Journal of Applied Physics, 2017, 56, 06GE04.	1.5	7
13	Band-like transport in highly crystalline graphene films from defective graphene oxides. Scientific Reports, 2016, 6, 28936.	3.3	68
14	Method for Controlling Electrical Properties of Single-Layer Graphene Nanoribbons via Adsorbed Planar Molecular Nanoparticles. Scientific Reports, 2015, 5, 12341.	3.3	21
15	Extraordinary suppression of carrier scattering in large area graphene oxide films. Applied Physics Letters, 2014, 105, .	3.3	28
16	Strain induced intermixing of Ge atoms in Si epitaxial layer on Ge(111). Journal of Applied Physics, 2013, 113, 073511.	2.5	0
17	Carrier Transport Properties of the Field Effect Transistors with Graphene Channel Prepared by Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2012, 51, 06FD03.	1.5	12
18	Influence of nanoparticle size to the electrical properties of naphthalenediimide on single-walled carbon nanotube wiring. Nanotechnology, 2012, 23, 215701.	2.6	5

#	Article	IF	CITATIONS
19	Fabrication and Developments of Nano-gap Electrode using Self-assembled Molecular Lithography. Journal of the Vacuum Society of Japan, 2012, 55, 333-340.	0.3	0
20	Carrier Transport Properties of the Field Effect Transistors with Graphene Channel Prepared by Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2012, 51, 06FD03.	1.5	12
21	Thickness Control of Graphene Overlayer via Layer-by-Layer Growth on Graphene Templates by Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2011, 50, 06GE04.	1.5	12
22	Layer-by-layer growth of graphene layers on graphene substrates by chemical vapor deposition. Thin Solid Films, 2011, 519, 6447-6452.	1.8	53
23	Fabrication of Nanogap Electrodes by the Molecular Lithography Technique. Japanese Journal of Applied Physics, 2011, 50, 035204.	1.5	4
24	Thickness Control of Graphene Overlayer via Layer-by-Layer Growth on Graphene Templates by Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2011, 50, 06GE04.	1.5	6
25	Strain induced modification of quasi-two-dimensional electron gas state on â^š3×â^š3-Ag structure. Journal of Applied Physics, 2010, 107, 084317.	2.5	7
26	The fabrication and single electron transport of Au nano-particles placed between Nb nanogap electrodes. Nanotechnology, 2010, 21, 225301.	2.6	12
27	Modification of electronic states of $\hat{a} = \hat{a} $	2.5	6
28	LOCAL ELECTRONIC STATES ON TWO-DIMENSIONAL NANOSCALE ISLAND OF Si AND Ge FABRICATED ON Si(111) 7 × 7 SUBSTRATE. International Journal of Nanoscience, 2009, 08, 595-603.	0.7	0
29	Fine Structure and Local Electronic States on Two-dimensional Nanoscale Islands of Si and Ge. Journal of the Vacuum Society of Japan, 2008, 51, 291-297.	0.3	0
30	I-V characteristics of single electron tunneling from symmetric and asymmetric double-barrier tunneling junctions. Applied Physics Letters, 2007, 90, 223112.	3.3	32
31	Growth of metallic Au adsorbed islands on the Si(111)-(7 \tilde{A} — 7) substrate. Journal of Physics: Conference Series, 2007, 61, 1056-1060.	0.4	1
32	Size-dependent single electron tunneling effect in Au nanoparticles. Surface Science, 2007, 601, 3907-3911.	1.9	25
33	Fabrication of uniform Au silicide islands on the Si(111)-($7 ilde{A}$ —7) substrate. Surface Science, 2006, 600, 1125-1128.	1.9	5
34	Fabrication of nanoscale gaps using a combination of self-assembled molecular and electron beam lithographic techniques. Applied Physics Letters, 2006, 88, 223111.	3.3	60
35	Strain and electronic structure of Ge nanoislands on Si(111)-7 $ ilde{A}$ —7surface. Physical Review B, 2005, 72, .	3.2	10
36	Electronic structures of dangling-bond states on the Si nanoisland and the Si(111) $7\tilde{A}$ –7 substrate. Journal of Applied Physics, 2005, 98, 063712.	2.5	4

#	Article	IF	CITATIONS
37	lonic-Electronic Conductor Nanostructures: Template-Confined Growth and Nonlinear Electrical Transport. Small, 2005, 1, 971-975.	10.0	62
38	Study of photoelectron spectroscopy from extremely uniform Si nanoislands on Si(111) $7\tilde{A}$ –7 substrate. Journal of Applied Physics, 2004, 96, 5013-5016.	2.5	11
39	Interrelations between the local electronic states and the atomic structures in the Si nanoscale island on Si(111)-(7 $ ilde{A}$ —7) surface. Journal of Applied Physics, 2003, 93, 4824-4830.	2.5	10
40	Local structure and electronic state of a nanoscale Si island on Si()- $7\tilde{A}$ – 7 substrate. Surface Science, 2002, 507-510, 582-587.	1.9	10
41	Nucleation of polycrystalline layer induced by formation of 30° partial dislocation during Si/Si() growth. Surface Science, 2002, 505, 225-233.	1.9	2
42	Surface roughening induced by a characteristic surface structure of a Si film grown on Si(111). Surface Science, 2001, 481, 67-77.	1.9	4